

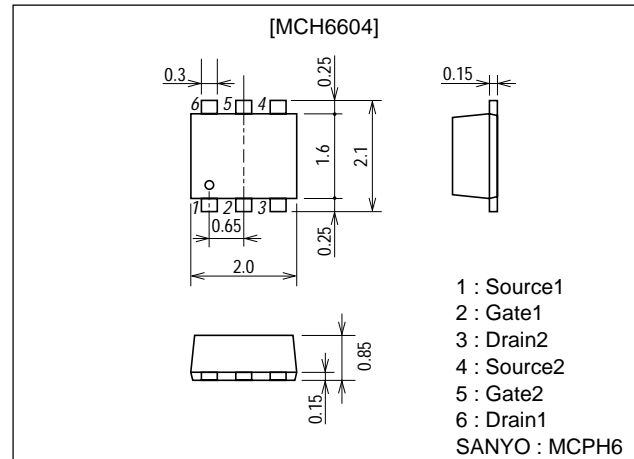
**MCH6604****Ultrahigh-Speed Switching Applications****Features**

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in one package, facilitating high-density mounting.

Package Dimensions

unit:mm

2173

**Specifications****Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		50	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		0.25	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	1	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0$	50			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=50V, V_{GS}=0$			10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=±8V, V_{DS}=0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=100μA$	0.4		1.3	V
Forward Transfer Admittance	yfs	$V_{DS}=10V, I_D=50mA$	130	180		mS
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=50mA, V_{GS}=4V$		6	7.8	Ω
	$R_{DS(on)2}$	$I_D=30mA, V_{GS}=2.5V$		7.1	9.9	Ω
	$R_{DS(on)3}$	$I_D=10mA, V_{GS}=1.5V$		10	20	Ω

Marking : FD

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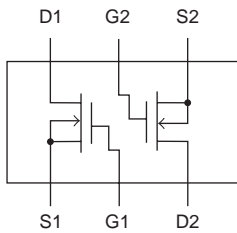
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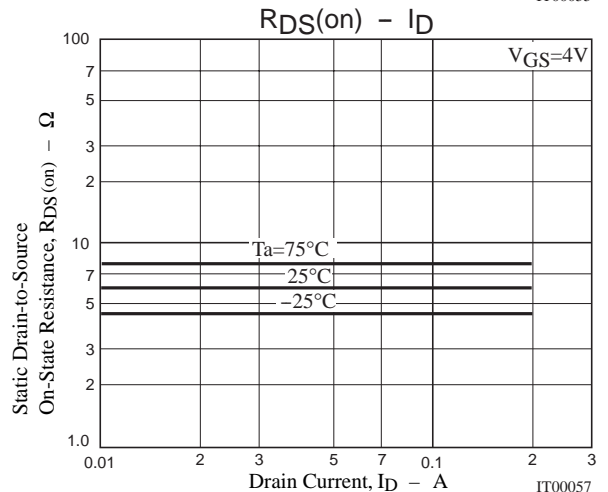
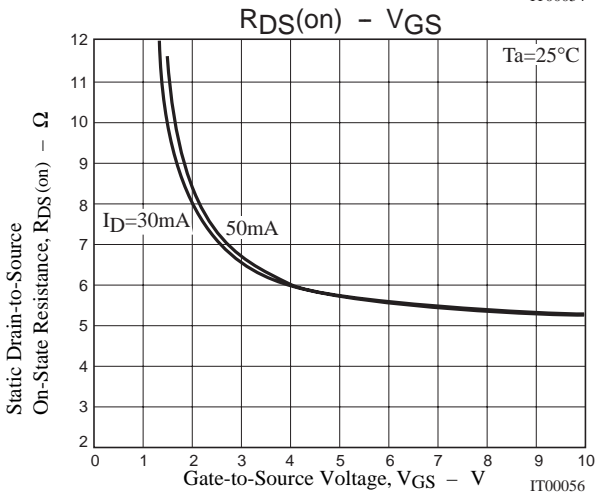
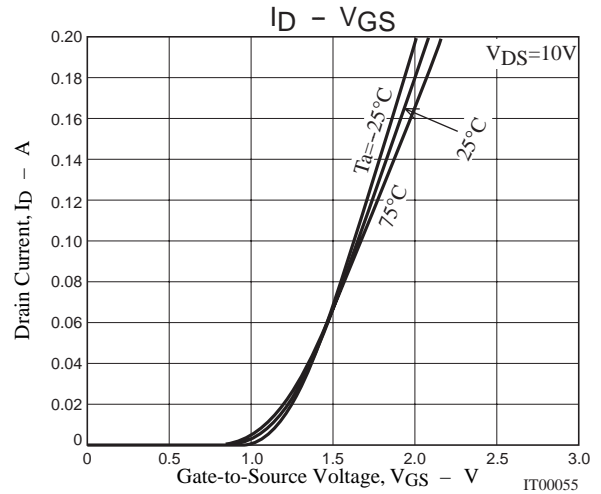
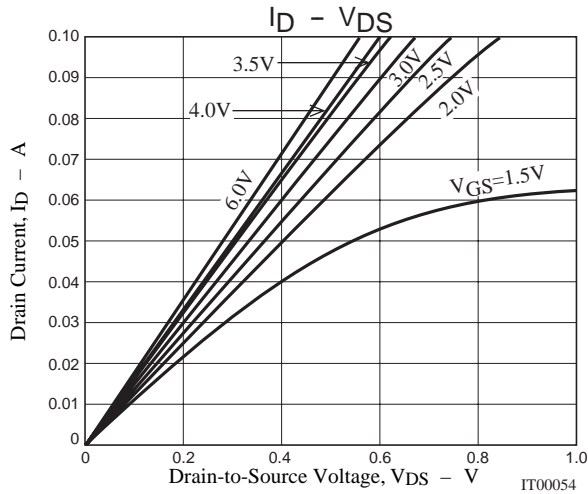
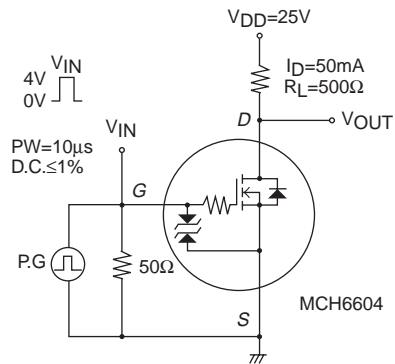
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=10V, f=1MHz$		6.6		pF
Output Capacitance	Coss	$V_{DS}=10V, f=1MHz$		4.7		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=10V, f=1MHz$		1.7		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		18		ns
Rise Time	t_r	See specified Test Circuit		42		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		190		ns
Fall Time	t_f	See specified Test Circuit		105		ns
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=10V, I_D=100mA$		1.57		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=10V, I_D=100mA$		0.20		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=10V, I_D=100mA$		0.32		nC
Diode Forward Voltage	V_{SD}	$I_S=100mA, V_{GS}=0$		0.85	1.2	V

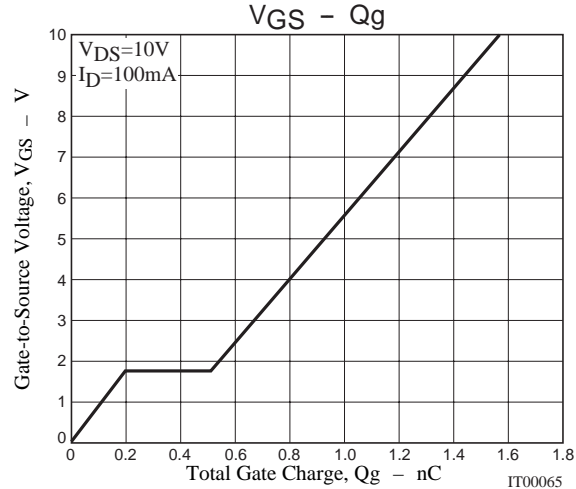
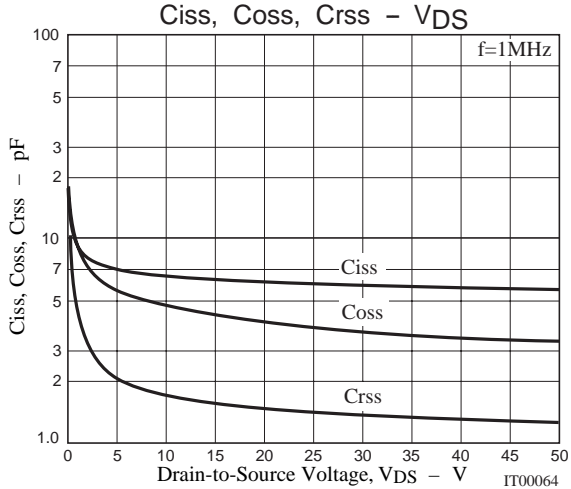
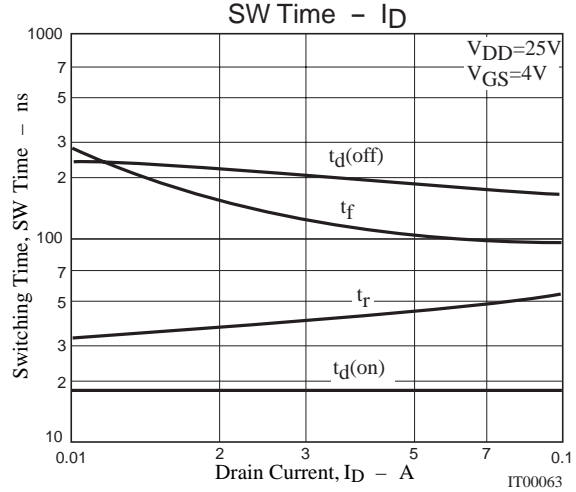
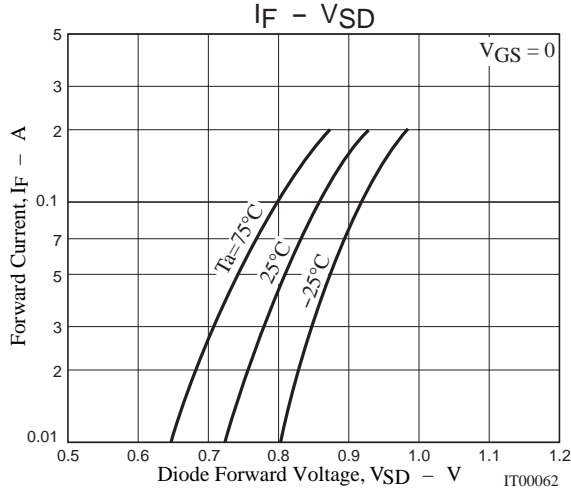
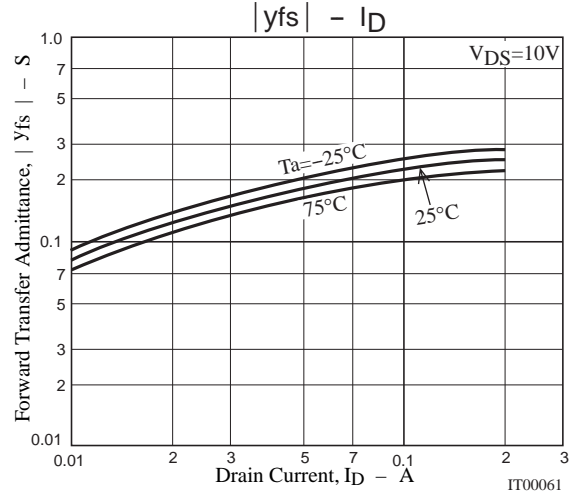
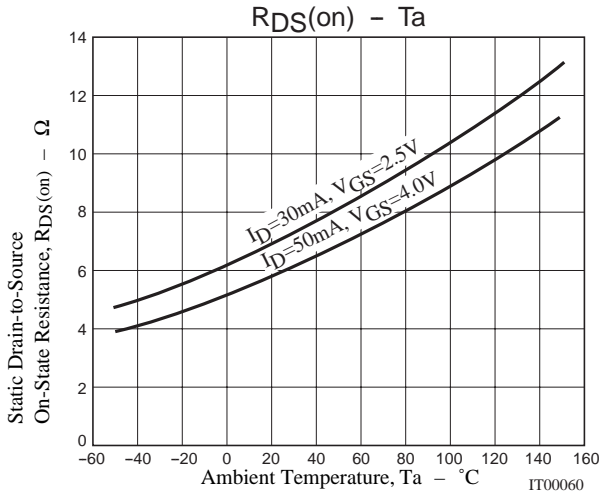
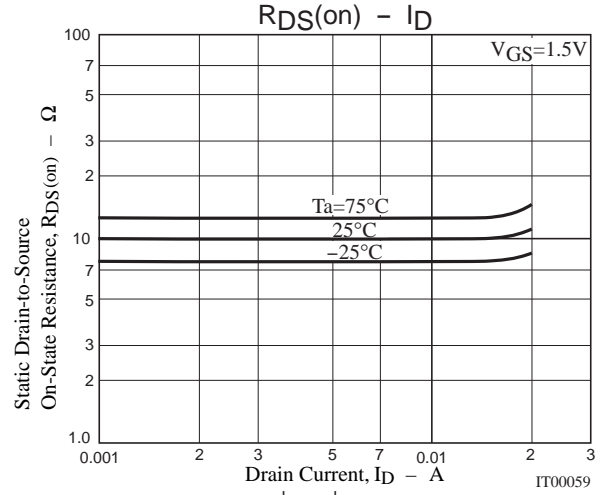
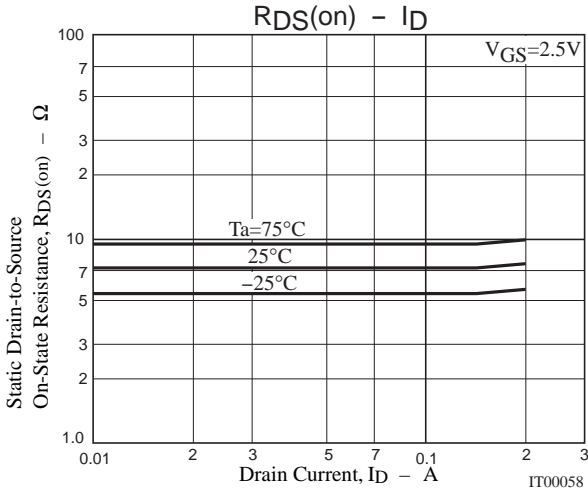
Electrical Connection



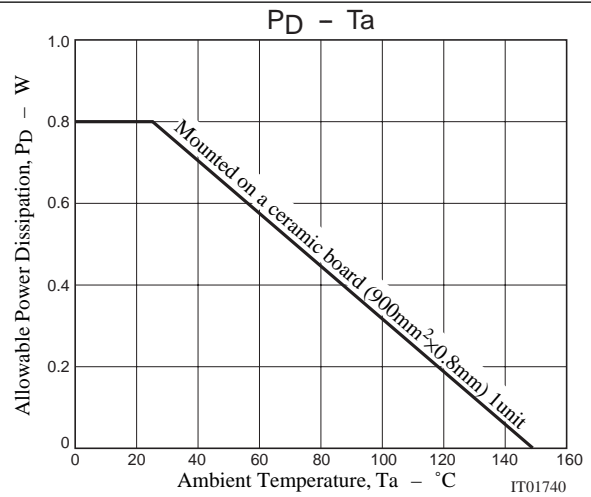
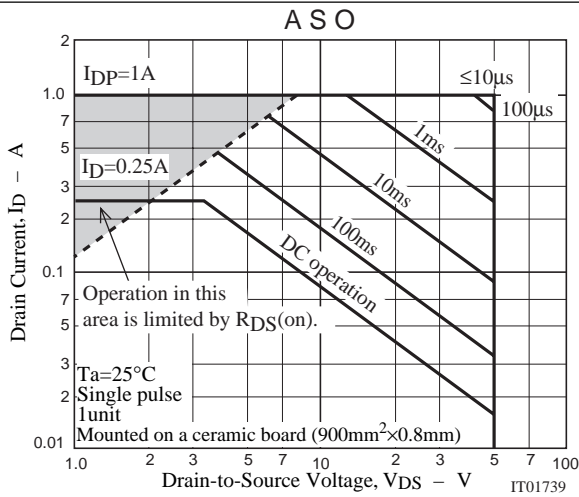
Switching Time Test Circuit



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